To all our customers

勝 特 力 材 料 886-3-5753170 胜特力电子(上海) 86-21-54151736 胜特力电子(深圳) 86-755-83298787 Http://www.100y.com.tw

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003



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Silicon NPN Epitaxial



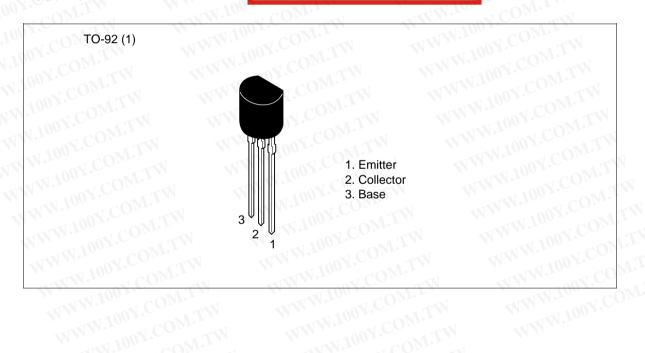
ADE-208-1062A (Z) 2nd. Edition Mar. 2001

Application

• Low frequency amplifier

Outline

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Absolute Maximum Ratings (Ta = 25°C)

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Item	Symbol	2SC2396	2SC2543	2SC2544	Unit
Collector to base voltage	V_{CBO}	60	90 0	120	V
Collector to emitter voltage	V _{CEO}	60	90	120	V
Emitter to base voltage	V_{EBO}	5	5,007.	5	V
Collector current	Ic	100	100	100	mA
Emitter current	Y. CE	–100	-100	-100	mA
Collector power dissipation	P _c	400	400	400	mW
Junction temperature	TiCOM	150	150	150	°C
Storage temperature	Tstg	-55 to +150	-55 to +150	-55 to +150	√ °C

Electrical Characteristics (Ta = 25°C)

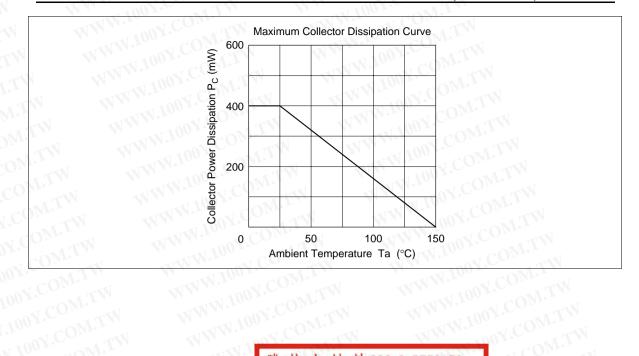
COM.TW	WWY	M.7	00X		M.T	W		WV	WW.	1002	I.CO	M.TW
Electrical Charac	cteristi	cs (7	$\Gamma a = 2$	25°C)	M.							
		2SC2396		2SC2543		2SC2544						
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	60	NW.	$I_{\overline{00},\overline{1}}$	90	M.	TW	120		MM	.V)V	$I_{\rm C} = 10 \ \mu \text{A}, \ I_{\rm E} = 0$
Collector to emitter breakdown voltage	V _{(BR)CEO}	60	AT A	N.100	90		VT.	120	- <		٧	$I_C = 1 \text{ mA},$ $R_{BE} =$
Emitter to base breakdown voltage	V _{(BR)EBO}	5	MA	W.19	5	.co	TI.	5	_	W	VV.	$I_E = 10 \ \mu A, \ I_C = 0$
Collector cutoff current	I _{CBO}	_	-V	0.1	400	Y.C.	0.1		_	0.1	μΑ	$V_{CB} = 50 \text{ V}, I_{E} = 0$
Emitter cutoff current	I _{EBO}	_		0.1	-	0 7 .0	0.1	TV	1—	0.1	μΑ	$V_{EB} = 2 \text{ V}, I_{C} = 0$
DC current transfer ratio	h _{FE} *1	250	- `,	1200	250	VOOY	1200	250	W.	800	WV	$V_{CE} = 12 \text{ V},$ $I_{C} = 2 \text{ mA}$
Collector to emitter saturation voltage	V _{CE(sat)}	N_		0.2	NW	1 0 0	0.2	JM.	LM LM	0.2	V	$I_C = 10 \text{ mA},$ $I_B = 1 \text{ mA}$
Base to emitter voltage	V _{BE}	TW	0.6	- 1	W.	0.6	0 <u>0</u> 7.C		0.6	N -	V	$V_{CE} = 12 \text{ V},$ $I_C = 2 \text{ mA}$
Gain bandwidth product	f _T		90	_		90	7002 1 0 02	Z.CC	90	TW	MHz	$V_{CE} = 12 \text{ V},$ $I_{C} = 2 \text{ mA}$
Collector output capacitance	Cob	\overline{M}	3.0	_	-11	3.0	N.700	y . C	3.0	_	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0,$ f = 1 MHz

1. The 2SC2396, 2SC2543 and 2SC2544 are grouped by $\rm h_{\rm FE1}$ as follows. Note:

MM	D.	E	F
2SC2396, 2SC2543	250 to 500	400 to 800	600 to 1200
2SC2544	250 to 500	400 to 800	_

See characteristic curves of 2SC2545, 2SC2546 and 2SC2547.

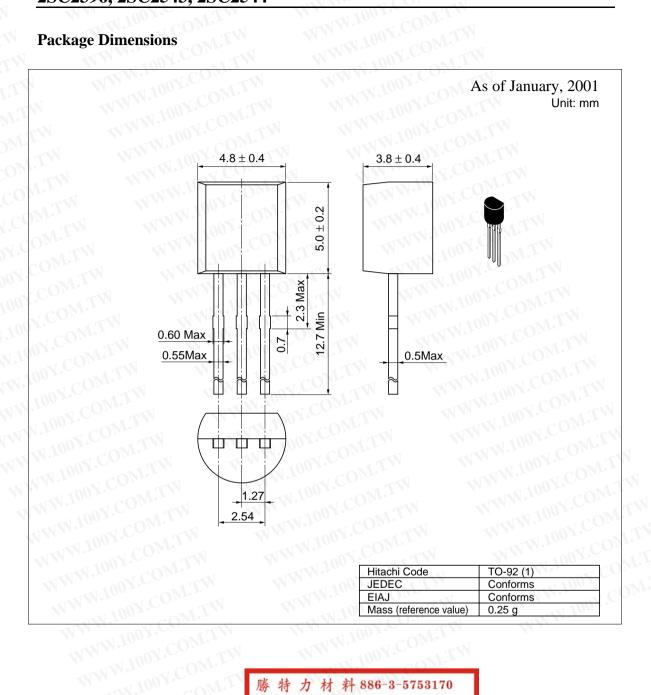
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Package Dimensions



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